

#### **60V P-CHANNEL ENHANCEMENT MODE MOSFET**

### **Product Summary**

V <sub>(BR)DSS</sub>	R <sub>DS(on)</sub> Max	I <sub>D</sub> Max T <sub>A</sub> = +25°C (Note 7)
-60V	125mΩ @ $V_{GS} = -10V$	-3.0 A
-60 V	190mΩ @ V <sub>GS</sub> = -4.5V	-2.4 A

### **Description**

This MOSFET is designed to minimize the on-state resistance and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

# **Applications**

- DC-DC Converters
- Power Management Functions
- Disconnect Switches
- Motor Control

#### **Features and Benefits**

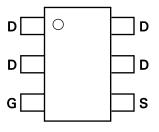
- Low On-Resistance
- Fast Switching Speed
- Low Threshold
- Low Gate Drive
- Low Input Capacitance
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Available (Note 4)

#### **Mechanical Data**

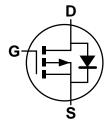
- Case: SOT26
- Case Material: Molded Plastic, "Green" Molding Compound;
  UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram Below
- Terminals: Finish Matte Tin Annealed over Copper Leadframe; Solderable per MIL-STD-202, Method 208 ©3
- Weight: 0.018 grams (Approximate)







Pin Out - Top View



Equivalent Circuit

#### Ordering Information (Notes 4 & 5)

Part Number	Compliance	Case	Quantity per reel	
ZXMP6A17E6QTA	Automotive	SOT26	3,000	

Note:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to http://www.diodes.com/quality/product\_grade\_definitions/.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

# **Marking Information**



6A17 = Product Type Marking Code YM = Date Code Marking Y or  $\overline{Y}$  = Year (ex: C = 2015) M or  $\overline{M}$  = Month (ex: 9 = September)

Date Code Key

Year	2015	2016	2017	2018	2019	2020	2021	2022	2023	2024	2025	2026
Code	С	D	Е	F	G	Н	1	J	K	L	М	N

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



# **Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

	Characteristic		Symbol	Value	Unit
Drain-Source Voltage			$V_{DSS}$	-60	V
Gate-Source Voltage			V <sub>GS</sub>	±20	V
		(Note 7)		-3.0	
Continuous Drain Current	$V_{GS} = 10V$	$T_A = +70^{\circ}C \text{ (Note 7)}$	$I_{D}$	-2.4	Α
		(Note 6)		-2.3	
Pulsed Drain Current	$V_{GS} = 10V$	(Note 8)	I <sub>DM</sub>	-13.6	Α
Continuous Source Current (Body Diode) (Note 7)		(Note 7)	Is	-2.5	Α
Pulsed Source Current (Bod	y Diode)	(Note 8)	I <sub>SM</sub>	-13.6	Α

# Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

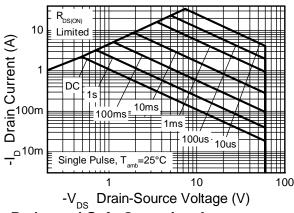
Characteristic	Characteristic			Unit
Power Dissipation	(Note 6)		1.1	
Linear Derating factor	(Note 7)	P <sub>D</sub>	1.92 15.4	mW/°C
Thermal Resistance, Junction to Ambient	(Note 6) (Note 7)	R <sub>θJA</sub>	113 65	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C	

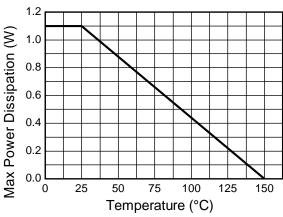
Notes:

- 6. For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
- 7. Same as Note 6, except the device is measured at  $t \le 5$  sec.
- 8. Same as Note 6, except the device is pulsed with D = 0.02 and pulse width 300 µs. The pulse current is limited by the maximum junction temperature.



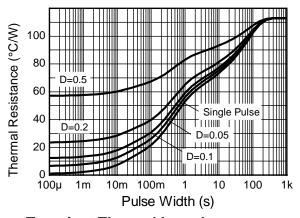
# **Thermal Characteristics**

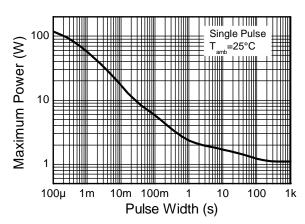




P-channel Safe Operating Area

**Derating Curve** 





**Transient Thermal Impedance** 

**Pulse Power Dissipation** 



# **Electrical Characteristics** (@ $T_A = \pm 25$ °C, unless otherwise specified.)

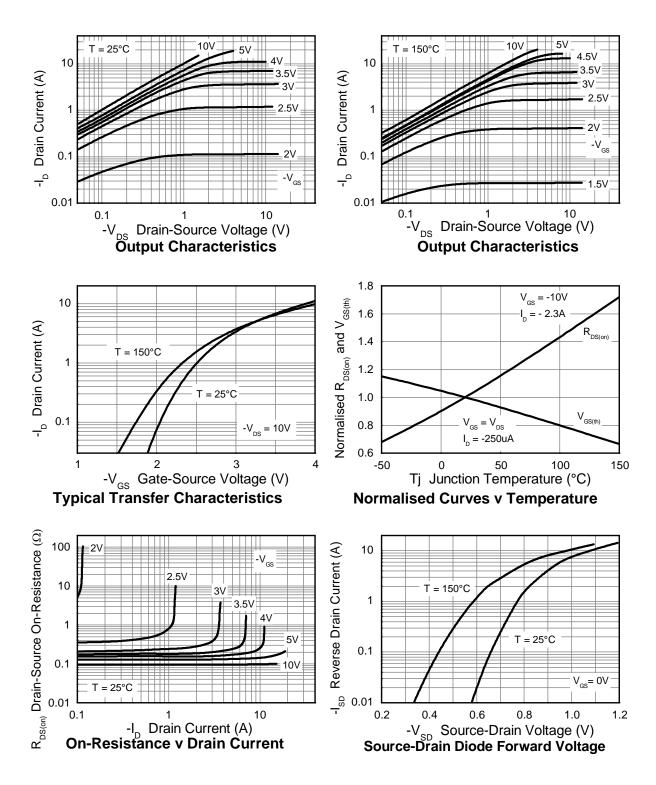
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition		
OFF CHARACTERISTICS								
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-60	_	_	V	$I_D = -250\mu A, V_{GS} = 0V$		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_	_	-1.0	μΑ	$V_{DS} = -60V, V_{GS} = 0V$		
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$		
ON CHARACTERISTICS								
Gate Threshold Voltage	V <sub>GS(th)</sub>	-1.0	_	-3.0	V	$I_D = -250 \mu A$ , $V_{DS} = V_{GS}$		
Statio Drain Source On Registence (Note 0)	D		0.100	0.125	Ω	$V_{GS} = -10V, I_D = -2.3A$		
Static Drain-Source On-Resistance (Note 9)	R <sub>DS</sub> (ON)		0.130	0.190	22	$V_{GS} = -4.5V$ , $I_{D} = -1.9A$		
Forward Transconductance (Notes 9 & 10)	g <sub>fs</sub>	_	4.7		S	$V_{DS} = -15V, I_{D} = -2.3A$		
Diode Forward Voltage (Note 9)	$V_{SD}$	_	-0.85	-0.95	V	I <sub>S</sub> = -2.0A, V <sub>GS</sub> = 0V		
Reverse Recovery Time (Note 10)	t <sub>rr</sub>		25.1		ns	1 170 di/dt 1000/up		
Reverse Recovery Charge (Note 10)	$Q_{rr}$	_	27.2	_	nC	I <sub>F</sub> = -1.7A, di/dt = 100A/μs		
DYNAMIC CHARACTERISTICS (Note 10)								
Input Capacitance	C <sub>iss</sub>	_	637	_	pF	\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \		
Output Capacitance	Coss	_	70		рF	$V_{DS} = -30V, V_{GS} = 0V$ - f = 1.0MHz		
Reverse Transfer Capacitance	Crss	_	53		рF	1 – 1.000112		
Total Gate Charge (Note 11)	$Q_g$	_	9.8	_	nC	$V_{GS} = -5.0V$		
Total Gate Charge (Note 11)	Qg	_	17.7	_	nC	V <sub>DS</sub> = -30V		
Gate-Source Charge (Note 11)	$Q_{gs}$	_	1.6	_	nC	$V_{GS} = -10V$ $I_{D} = -2.3A$		
Gate-Drain Charge (Note 11)	$Q_{gd}$	_	4.4	_	nC			
Turn-On Delay Time (Note 11)	t <sub>D(on)</sub>	_	2.6	_	ns			
Turn-On Rise Time (Note 11)	t <sub>r</sub>	_	3.4	_	ns	$V_{DD} = -30V, V_{GS} = -10V$		
Turn-Off Delay Time (Note 11)	t <sub>D(off)</sub>	_	26.2	_	ns	$I_D = -1.0A, R_G \cong 6.0\Omega$		
Turn-Off Fall Time (Note 11)	t <sub>f</sub>	_	11.3	_	ns			

Notes:

Measured under pulsed conditions. Pulse width ≤ 300µs; duty cycle ≤ 2%.
 For design aid only, not subject to production testing.
 Switching characteristics are independent of operating junction temperatures.

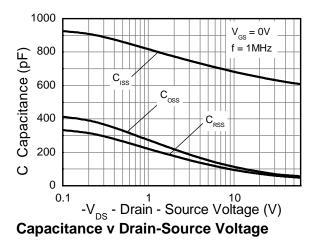


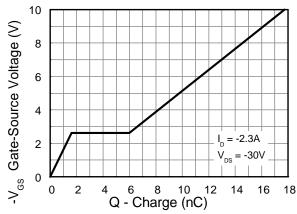
# **Typical Characteristics**





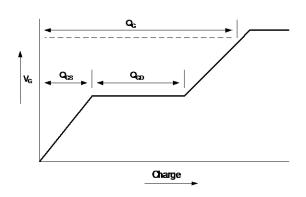
### Typical Characteristics (cont.)

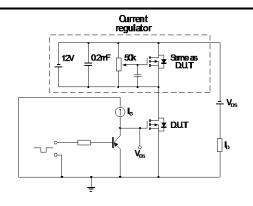




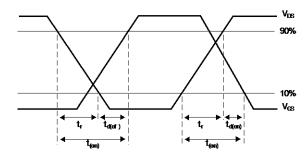
**Gate-Source Voltage v Gate Charge** 

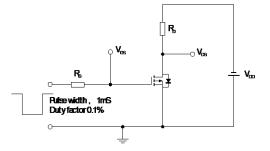
### **Test Circuits**





Basic gate charge waveform Gate charge test circuit





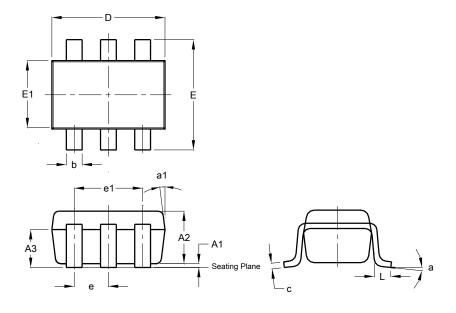
Switching time waveforms

Switching time test circuit



# **Package Outline Dimensions**

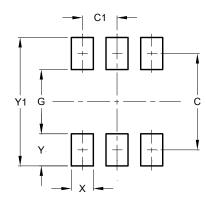
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



	SC	)T26						
Dim	Min	Max	Тур					
A1	0.013	0.10	0.05					
A2	1.00	1.30	1.10					
A3	0.70	0.80	0.75					
b	0.35	0.50	0.38					
С	0.10	0.20	0.15					
D	2.90	3.10	3.00					
е	-	-	0.95					
e1	-	-	1.90					
Е	2.70	3.00	2.80					
E1	1.50	1.70	1.60					
L	0.35	0.55	0.40					
а	-	-	8°					
a1	-	-	7°					
All	All Dimensions in mm							

# **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	2.40
C1	0.95
G	1.60
Х	0.55
Y	0.80
Y1	3.20



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